

### 1000V 6A 2.1Ω N-ch Power MOSFET

# **Description**

WMOS D1 is Wayon's 1<sup>st</sup> generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.



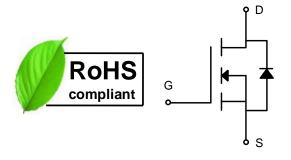


### **Features**

- Typ.R<sub>DS(on)</sub>=2.1 $\Omega$ @V<sub>GS</sub>=10V
- 100% avalanche tested
- RoHS Compliant

# **Applications**

- SMPS
- Charger
- DC-DC



### **Absolute Maximum Ratings** (T<sub>C</sub>=25℃)

Parameter	Symbol	WML6N100D1	WMM6N100D1	Unit
Drain-source voltage	V <sub>DSS</sub>	10	000	V
Gate-source Voltage	V <sub>G</sub> S	<u>+</u>	:30	V
Continuous drain current	ID		6	А
Pulsed drain current <sup>1</sup>	Ірм	,	24	А
Avalanche energy, single pulse <sup>2</sup>	Eas	122		mJ
Power dissipation	PD	65		W
Derate above 25°C		0.52		W/°C
Operating junction temperature	Tj	-55~150		℃
Storage temperature	T <sub>stg</sub>	-55~150		℃
Continuous diode forward current	Is	6		А
Diode pulse current	I <sub>Spulse</sub> 1	-	24	А

### **Thermal Characteristic**

Thermal resistance,junction-to-case	$R_{ heta JC}$	1.92	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	80	°C/W





Electrical	Charac	teristics	of MOSFE	ΞΤ
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Drain-source breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	Tc=25°C	1000	-	-	V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	TJ=25°C	3.5	-	4.5	V
Drain-source leakage current	la a a	V <sub>DS</sub> =1000V, V <sub>GS</sub> =0V	TJ=25°C	-	-	1	μA
	IDSS	V <sub>DS</sub> =800V, V <sub>GS</sub> =0V	TJ=125°C	-	-	100	μA
Gate-source leakage current,forward	IGSSF	V <sub>DS</sub> =0V, V <sub>GS</sub> =30V	TJ=25°C	-	-	100	nA
Gate-source leakage current,reverse	Igssr	V <sub>DS</sub> =0V, V <sub>GS</sub> =-30V	TJ=25°C	-	-	-100	nA
Drain-source on-state resistance <sup>3</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	TJ=25°C	-	2.1	2.3	Ω
Transconductance <sup>3</sup>	Gfs	V <sub>DS</sub> =20V	TJ=25°C	-	10	-	S

# **Dynamic Characteristics of MOSFET** $(T_C=25^{\circ}C)$

Dynamic Characteristics of	WIOSI LI	(TC=25 C)	Min.	Тур.	Max.	
Input capacitance	Ciss	f=1MHz, V <sub>DS</sub> =25V,	-	1773	-	pF
Output capacitance	Coss	$V_{GS}=0$ V	-	125	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	VGS=0V	-	25	-	pF
Gate to source charge	Q <sub>gs</sub>	V <sub>DD</sub> =275V	-	9	-	nC
Gate to drain charge	$Q_{gd}$	I <sub>D</sub> =6A	-	12	-	nC
Total gate charge	Qg	V <sub>GS</sub> = 0 to10V	-	40	-	nC

# Switching Characteristics of MOSFET (Tc=25°C)

			Min.	Typ.	Max.	
Turn-on delay time	t <sub>d on</sub>		-	32	-	ns
Rise time	t <sub>r</sub>	V <sub>DS</sub> =500V, I <sub>D</sub> =6A,	-	20	-	ns
Turn-off delay time	t <sub>d off</sub>	$R_G=4.7\Omega$ , $V_{GS}=0$ to $10V$ ,	-	128	-	ns
Fall time	t <sub>f</sub>		-	26	-	ns

# Characteristics of Body Diode (Tc=25℃)

Characteristics of body blode (1c=25 c)			Min.	Тур.	Max.	
Forward voltage	$V_{SD}$	I <sub>SD</sub> =6A, V <sub>GS</sub> =0V	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub>	V <sub>DS</sub> =500V, I <sub>s</sub> =6A,	-	318	-	ns
Reverse recovery current	Irr	V <sub>GS</sub> =10V	-	15	-	Α
Recovery charge	Qrr	-di/dt=100A/μs	-	2.4	-	μC

### Notes:

- 1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$  =150°C.
- 2. The E\_{AS} data shows Max. rating . The test condition is V\_DD =50V, V\_GS =10V, L=20mH, I\_{AS} =3.5A, Tc=25 ^{\circ}C .
- 3. The data tested by pulsed , pulse width  $\leq 300 \mu s$  , duty cycle  $\leq 2\%.$



### TYPICAL CHARACTERISTICS

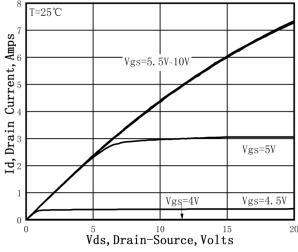


Figure 1.On-Region Characteristics

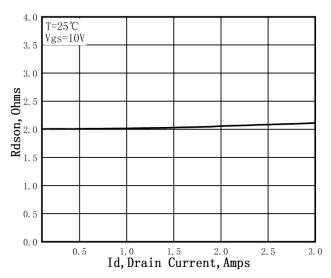


Figure 3. Static Drain-Source On Resistance

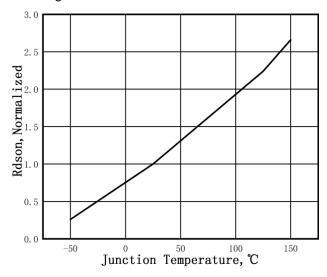


Figure 5. Normalized  $R_{DS(on)}$  vs.Temperature

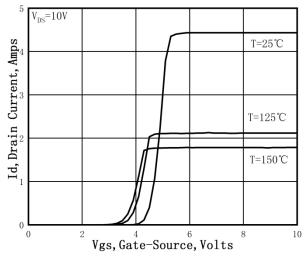


Figure 2. Transfer Characteristics

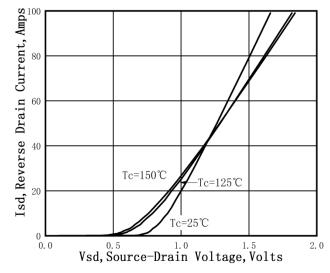


Figure 4. Typical Body Diode Transfer Characteristics

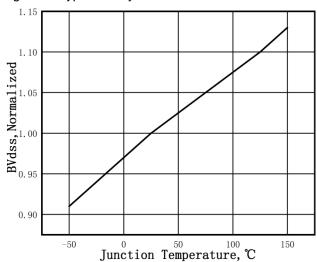
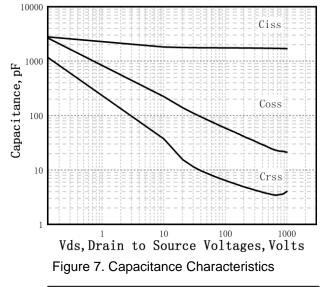
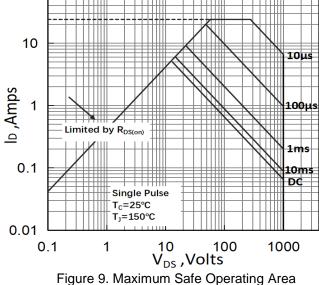


Figure 6. Normalized BV<sub>DSS</sub> vs.Temperature





(TO-220F)

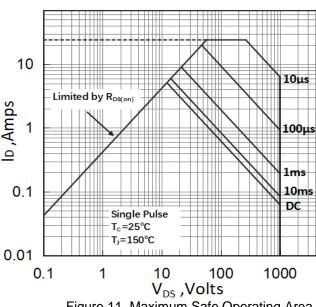


Figure 11. Maximum Safe Operating Area (TO-263)

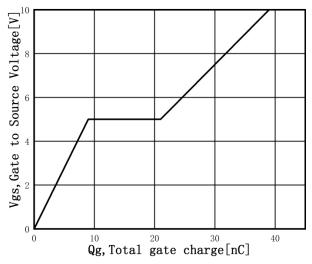


Figure 8. Gate Charge Characteristics

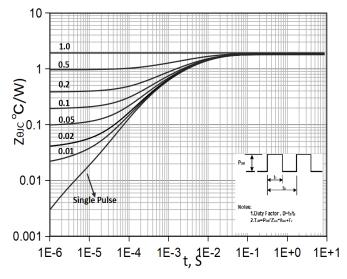


Figure 10. Typical Body Diode Transfer Characteristics (TO-220F)

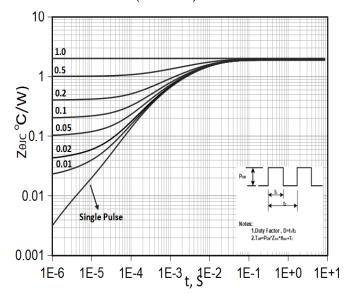


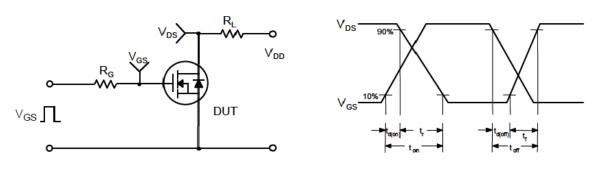
Figure 12. Typical Body Diode Transfer Characteristics (TO-263)



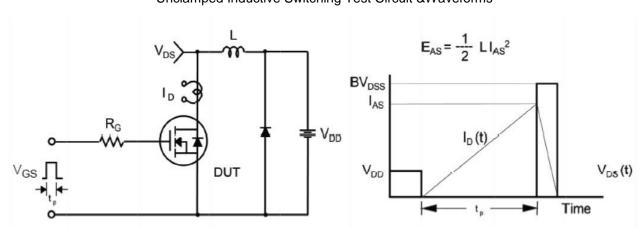
# **Test Circuit**

# Gate Charge Test Circuit &Waveform Vos Vos Charge

# Switching Test Circuit &Waveforms

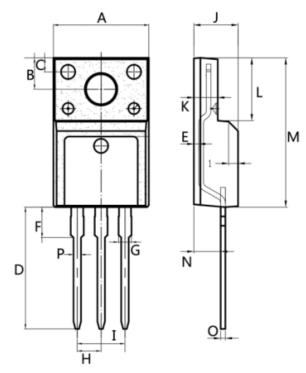


### Unclamped Inductive Switching Test Circuit &Waveforms

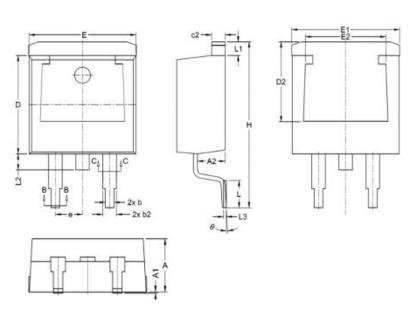




### **Mechanical Dimensions for TO-220F**



**Mechanical Dimensions for TO-263** 



### **COMMON DIMENSIONS**

SYMBOL	M	M
STIVIDOL	MIN	MAX
Α	9.95	10.36
В	2.95	3.55
С	1.25	1.6
D	12.64	13.5
E	0.40	0.60
F	2.80	3.80
G	1.14	1.58
Н	2.44	2.64
I	4.88	5.26
J	4.50	4.90
K	2.34	2.80
L	6.48	6.90
М	15.40	16.07
N	2.66	3.50
0	0.40	0.64
Р	0.70	0.94

### **COMMON DIMENSIONS**

SYMBOL	IV	IM
STIVIDOL	MIN	MAX
Α	4.45	4.65
A1	0	0.15
A2	2.50	2.70
b	0.75	0.96
b1	0.71	0.92
b2	1.21	1.41
b3	1.17	1.37
С	0.33	0.52
c1	0.28	0.48
c2	1.21	1.41
D	9.10	9.30
D2	7.21	7.62
Е	9.90	10.10
E1	9.90	10.30
E2	7.34	7.74
е	2.50	2.60
Н	15.30	15.70
L	2.34	2.74
L1	1.06	1.47
L2	1.40	1.60
L3	0.25	0.26



# **Ordering Information**

Part	Package	Marking	Packing method
WML6N100D1	TO-220F	WML6N100D1	Tube
WMM6N100D1	TO-263	WMM6N100D1	Tape and reel

# **Contact Information**

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201207 Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: http://www.way-on.com

For additional information, please contact your local Sales Representative.

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### **Product Specification Statement**

1. The product specification aims to provide users with a reference regarding various product parameters, performance, and usage. It presents certain aspects of the product's performance in graphical form and is intended solely for users to select product and make product comparisons, enabling users to better understand and evaluate the characteristics and advantages of the product. It does not constitute any commitment, warranty, or guarantee.

2.The product parameters described in the product specification are numerical values, characteristics, and functions obtained through actual testing or theoretical calculations of the product in an independent or ideal state. Due to the complexity of product applications and variations in test conditions and equipment, there may be slight fluctuations in parameter test values. WAYON shall not guarantee that the actual performance of the product when installed in the customer's system or equipment will be entirely consistent with the product specification, especially concerning dynamic parameters. It is recommended that users consult with professionals for product selection and system design. Users should also thoroughly validate and assess whether the actual parameters and performance when installed in their respective systems or equipment meet their requirements or expectations. Additionally, users should exercise caution in verifying product compatibility issues, and WAYON assumes no responsibility for the application of the product.

3.WAYON strives to provide accurate and up-to-date information to the best of our ability. However, due to technical, human, or other reasons, WAYON cannot guarantee that the information provided in the product specification is entirely accurate and error-free. WAYON shall not be held responsible for any losses or damages resulting from the use or reliance on any information in these product specifications. WAYON reserves the right to revise or update the product specification and the products at any time without prior notice, and the user's continued use of the product specification is considered an acceptance of these revisions and updates. Prior to purchasing and using the product, users should verify the above information with WAYON to ensure that the product specification is the most current, effective, and complete. If users are particularly concerned about product parameters, please consult WAYON in detail or request relevant product test reports. Any data not explicitly mentioned in the product specification shall be subject to separate agreement.

4.Users are advised to pay attention to the parameter limit values specified in the product specification and maintain a certain margin in design or application to ensure that the product does not exceed the parameter limit values defined in the product specification. This precaution should be taken to avoid exceeding one or more of the limit values, which may result in permanent irreversible damage to the product, ultimately affecting the quality and reliability of the system or equipment.

5. The design of the product is intended to meet civilian needs and is not guaranteed for use in harsh environments or precision equipment. It is not recommended for use in systems or equipment such as medical devices, aircraft, nuclear power, and similar systems, where failures in these systems or equipment could reasonably be expected to result in personal injury. WAYON shall assume no responsibility for any consequences resulting from such usage.

6.Users should also comply with relevant laws, regulations, policies, and standards when using the product specification. Users are responsible for the risks and liabilities arising from the use of the product specification and must ensure that it is not used for illegal purposes. Additionally, users should respect the intellectual property rights related to the product specification and refrain from infringing upon any third-party legal rights. WAYON shall assume no responsibility for any disputes or controversies arising from the above-mentioned issues in any form.

